Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device ~~provided with~~ comprising:

high concentration source[[/]] and drain layers of [[the]] a reverse conductive type formed in a semiconductor layer of one conductive type,

a gate electrode formed on a channel layer located between the source and drain layers,

a body layer of one conductive type ~~formed in the vicinity of~~ in direct contact with the high concentration source layer, and

a low concentration drain layer of the reverse conductive type formed between the channel layer and the drain layer, wherein:

said body layer is formed only under said gate electrode.

2. (Currently Amended) A semiconductor device, according to claim 1, wherein the ~~device comprises: a~~ gate electrode is formed on ~~a semiconductor~~ the channel layer ~~of one conductive type~~ via a gate oxide film;

wherein the [[a]] high concentration source layer ~~of the reverse conductive type formed so that it~~ is adjacent to one end of said gate electrode;

wherein the [[a]] high concentration drain layer ~~of the reverse conductive type~~ is formed apart from ~~the~~ an other end of said gate electrode;

wherein the [[a]] low concentration drain layer ~~of the reverse conductive type extended~~ extends from under said gate electrode and ~~formed so that said low concentration drain layer of the reverse conductive type~~ surrounds said high concentration drain layer ~~of the reverse conductive type~~; and

wherein the [[a]] body layer ~~of one conductive type under said gate electrode~~ is formed between said high concentration source layer ~~of the reverse conductive type~~ and said high concentration drain layer ~~of the reverse conductive type~~.

3. (Canceled)

4. (Currently Amended) A semiconductor device according to claim 1, wherein:

said low concentration drain layer is ~~of the reverse conductive type or said low concentration source/drain layers of the reverse conductive type are formed so that they are~~ shallow under said gate electrode and ~~are~~ deep under said high concentration drain layer ~~of the reverse conductive type or said high concentration source/drain layers of the reverse conductive type~~.

5. (Original) A semiconductor device, according to claim 1, wherein a reverse conductive type layer is formed in a surface portion of the body layer.

6-21. (Cancelled).

22. (New) A semiconductor device comprising:

high concentration source and drain layers of a reverse conductive type formed in a semiconductor layer of one conductive type;

a gate electrode on a channel layer located between the high concentration source and drain layers and formed via a gate oxide film;

a body layer of one conductive type formed only under the gate electrode and formed apart from the high concentration source and drain layers; and

low concentration source and drain layers of the reverse conductive type respectively surrounding said high concentration source layer and said high concentration drain layer;

wherein the low concentration source and drain layers are separated from each other by the body layer; and

wherein the body layer is in direct contact with the low concentration source and drain layers.

23. (New) The semiconductor device of claim 22 wherein said low concentration source and drain layers are shallow under said gate electrode and deep under said high concentration source and drain layers.

Amendments to the Drawings:

The attached replacement sheet of drawings includes changes to Fig. 14 and replaces the original sheet including Fig. 14.

In Figure 14, the legend "Prior Art" has been added.

Attachments following last page of this Amendment:

Replacement Sheet (1 pages)
Annotated Sheet Showing Change(s) (1 pages)